

## GaAs DPDT Diversity Switch

### 0.5 - 3.0 GHz

Rev. V5

#### Features

- Low Insertion Loss 0.7 dB at 2.4 GHz
- Low Cost 3 mm 12-Lead PQFN Package
- Ideal for WLAN IEEE 802.11b
- 0.5 micron GaAs pHEMT Process

#### Description

M/A-COM's MASWSS0040 is a GaAs pHEMT MMIC DPDT diversity switch in a low cost miniature 3 mm 12-lead PQFN package. The MASWSS0040 is ideally suited for applications where very small size and low cost are required.

Typical applications are for WLAN IEEE 802.11b/g systems that employ two antennas for transmit and receive diversity. This part is designed for low insertion loss and allows for independent control and selection of each switch path. This part can be used in all systems operating up to 3.0 GHz requiring moderate power and diversity switching.

The MASWSS0040 is fabricated using a 0.5 micron gate length GaAs pHEMT process. The process features full passivation for performance and reliability.

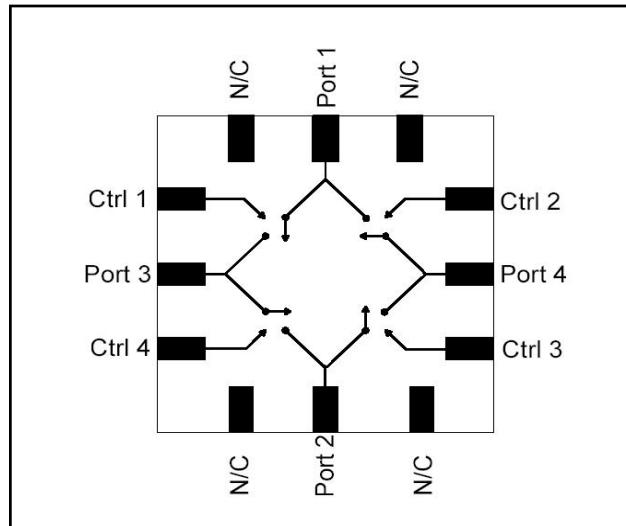
#### Ordering Information <sup>1,2</sup>

Part Number	Package
MASWSS0040	Bulk Packaging
MASWSS0040TR	1000 piece reel
MASWSS0040TR-3000	3000 piece reel
MASWSS0040SMB	Sample Test Board 0.5 - 3.0 GHz Tuning

1. Reference Application Note M513 for reel size information.

2. All sample boards include 5 loose parts.

#### Functional Schematic



#### Pin Configuration

Pin No.	Pin Name	Description
1	Ctrl 1	Control 1
2	Port 3	RF Port 3
3	Ctrl 4	Control 4
4	N/C	No Connection
5	Port 2	RF Port 2
6	N/C	No Connection
7	Ctrl 3	Control 3
8	Port 4	RF Port 4
9	Ctrl 2	Control 2
10	N/C	No Connection
11	Port 1	RF Port 1
12	N/C	No Connection
Pad	Paddle <sup>3</sup>	No Connection

3. The exposed pad centered on the package bottom must be connected to the RF and DC ground.

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Electrical Specifications:  $T_A = 25^\circ\text{C}$ ,  $V_C = 3 \text{ V}$ ,  $P_{IN} = 10 \text{ dBm}$ ,  $Z_0 = 50 \Omega$ 

Parameter	Test Conditions	Units	Min.	Typ.	Max.
Insertion Loss <sup>4</sup>	0.5 - 1.0 GHz	dB	—	0.5	1.2
	1.0 - 2.0 GHz	dB	—	0.6	1.2
	2.0 - 2.5 GHz	dB	—	0.7	1.2
	2.5 - 3.0 GHz	dB	—	0.8	1.2
Isolation <sup>5</sup>	0.5 - 1.0 GHz	dB	17.0	28.0	—
	1.0 - 2.0 GHz	dB	17.0	21.0	—
	2.0 - 2.5 GHz	dB	17.0	19.0	—
	2.5 - 3.0 GHz	dB	17.0	18.0	—
Return Loss	0.5 - 3.0 GHz	dB	—	20	—
IP3	Two Tone +5 dBm, 5 MHz Spacing, > 50 MHz	dBm	—	47	—
	$V_C = 0.2 \text{ V} / 2.3 \text{ V}$			52	—
P1dB	$V_C = 0.2 \text{ V} / 2.3 \text{ V}$	dBm	—	26	—
	$V_C = 0.2 \text{ V} / 3.0 \text{ V}$	dBm	—	31	—
2 <sup>nd</sup> Harmonic	2.4 GHz, $P_{IN} = 20 \text{ dBm}$ , $V_C = 0.2 \text{ V} / 2.5 \text{ V}$	dBc	—	70	—
3 <sup>rd</sup> Harmonic	2.4 GHz, $P_{IN} = 20 \text{ dBm}$ , $V_C = 0.2 \text{ V} / 2.5 \text{ V}$	dBc	—	60	—
Trise, Tfall	10% to 90% RF and 90% to 10% RF	ns	—	12/20	—
Ton, Toff	50% Control to 90% RF	ns	—	35	—
	50% Control to 10% RF	ns	—	40	—
Control Current	$ V_C  = 3 \text{ V}$	$\mu\text{A}$	—	5	25

4. Insertion Loss can be optimized by varying the DC Blocking Capacitor value, i.e. 1000 pF for 100 MHz - 1.0 GHz, 27 pF for 0.5 - 3.0 GHz.

5. Isolation of two paths on either side of the selected path.

Absolute Maximum Ratings <sup>6,7</sup>

Parameter	Absolute Maximum
Input Power 3V Control	+32 dBm
Input Power 5V Control	+34 dBm
Operating Voltage	+8.5 volts
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C

6. Exceeding any one or combination of these limits may cause permanent damage to this device.

7. M/A-COM does not recommend sustained operation near these survivability limits.

## Handling Procedures

Please observe the following precautions to avoid damage:

## Static Sensitivity

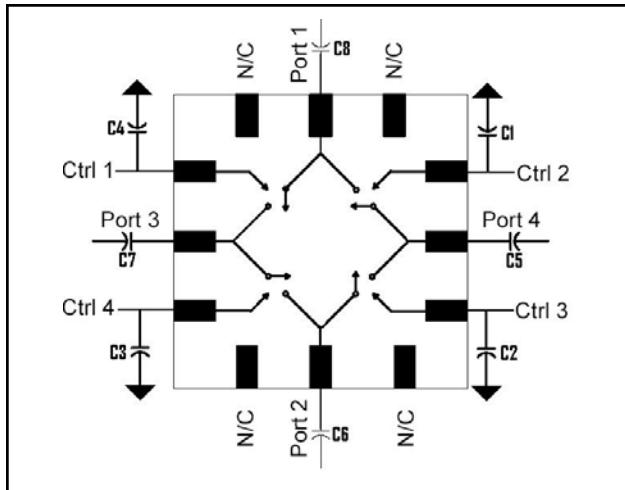
Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

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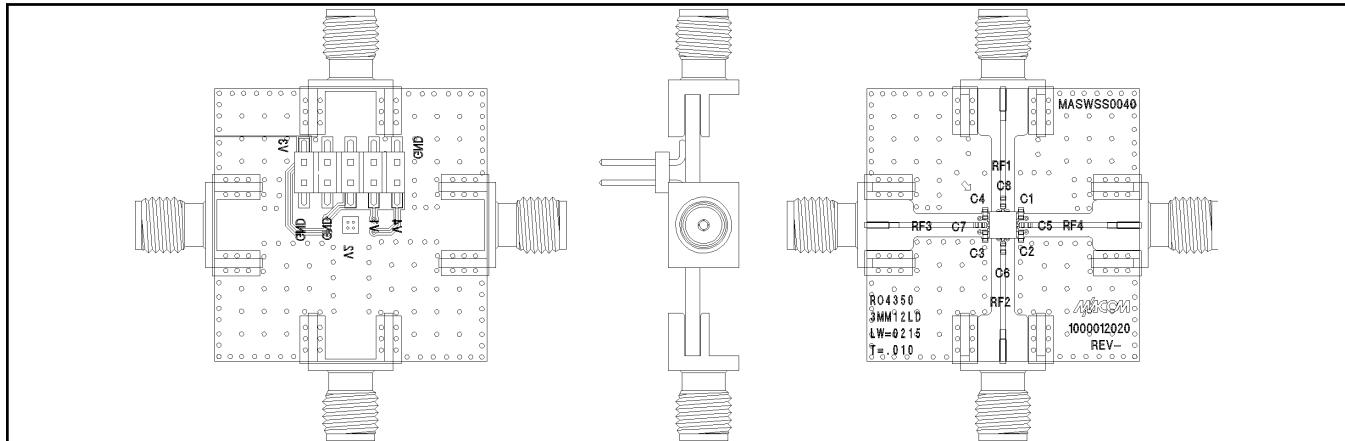
### Circuit Block Diagram



### Parts List

Part	Description
C1 – C4	27 pF Decoupling Capacitor
C5 – C8	27 pF DC Blocking Capacitor
RF1 – RF4	RF connector
Item 3	10-pin solder connector

### Evaluation Board MASWSS0040



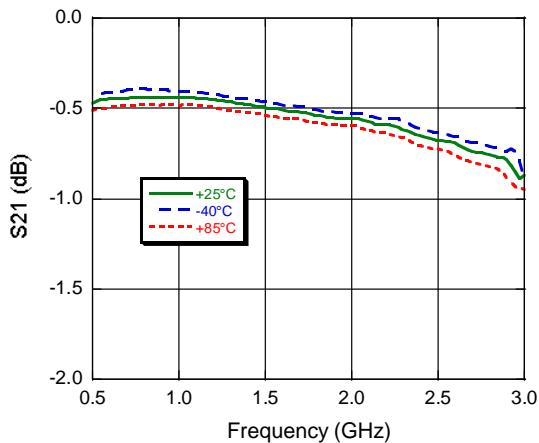
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### 0.5 - 3.0 GHz

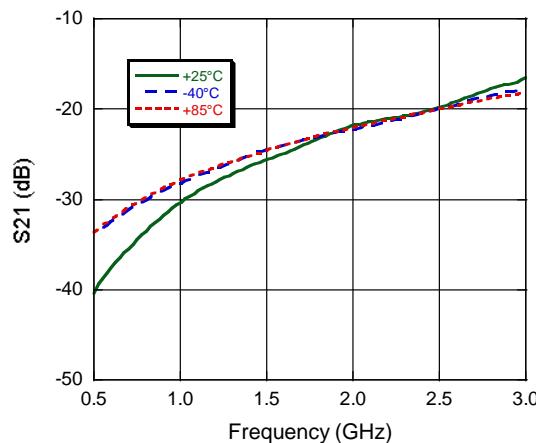
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### Typical Performance Curves

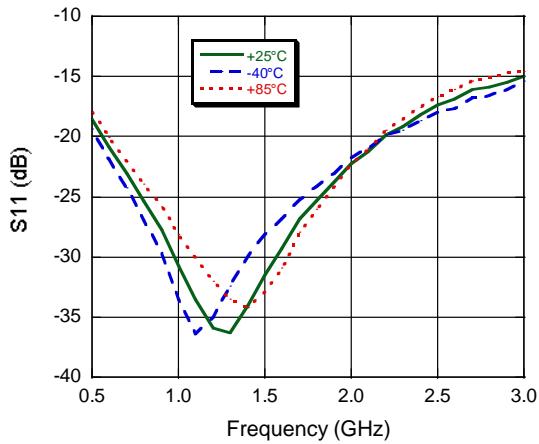
Insertion Loss, 27 pF



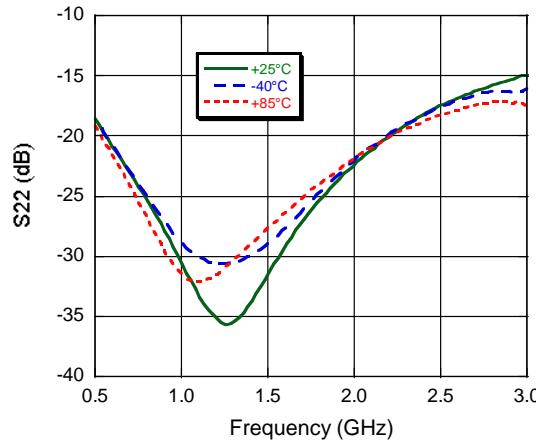
Isolation, 27 pF



Input Return Loss



Output Return Loss

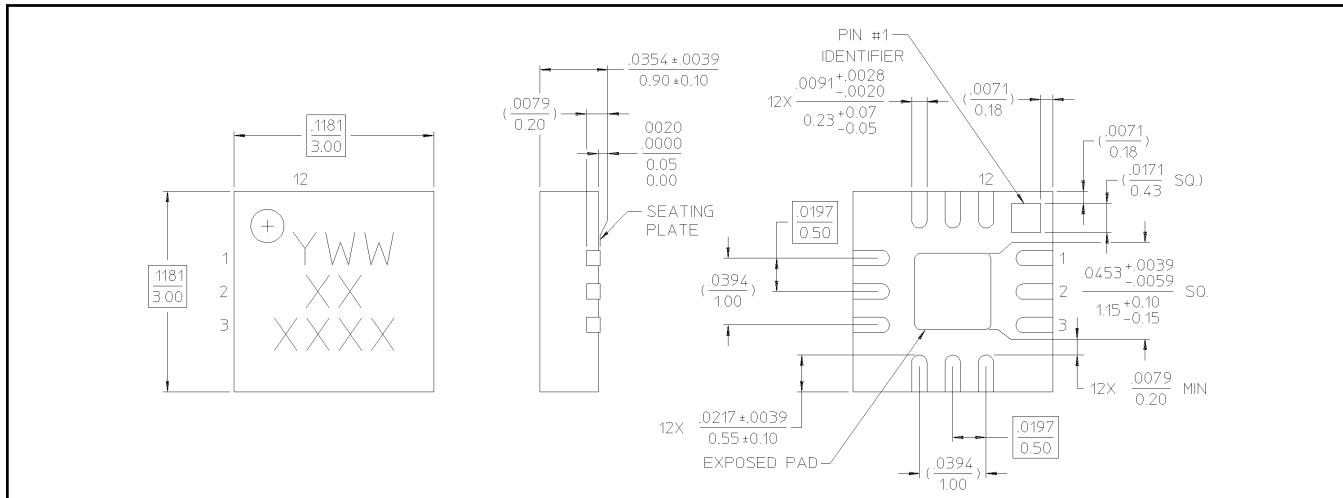


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#### 3 mm 12-Lead PQFN<sup>†</sup>



† Meets JEDEC moisture sensitivity level 1 requirements

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ Р В 0015-002 и ЭС РД 009

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